PU3226

Silicon NPN Triple-Diffused Planar Type

Power Amplifier

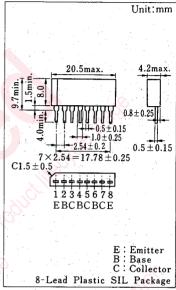
■ Features

- High DC current gain (hFE) and good linearity
- Low collector-emitter saturation voltage (V_{CE(sat)})
- 3 PNP elements

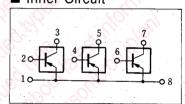
■ Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit		
Collector-base voltage	V _{CBO}	-60	V		
Collector-emitter voltage	V_{CEO}	-60	V		
Emitter-base voltage	V_{EBO}	-6	V		
Peak collector current	I _{CP}	-4	A		
Collector current	$I_{\mathbb{C}}$	-2	Α		
Power dissipation	P_{D}	15	w .		
Junction temperature	$T_{\rm j}$	150	°C		
Storage temperature	$T_{ m stg}$	-55~+150	°C(9)		

■ Package Dimensions

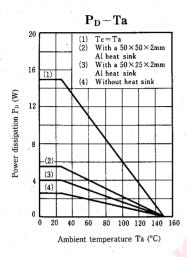


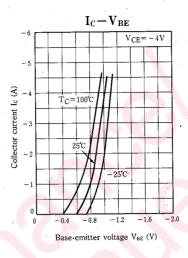
■ Inner Circuit

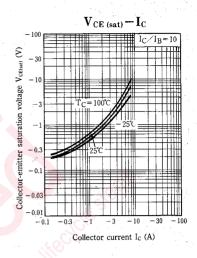


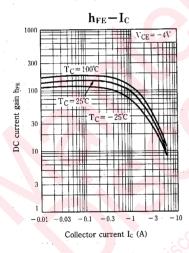
■ Electrical Characteristics (Tc=25°C)

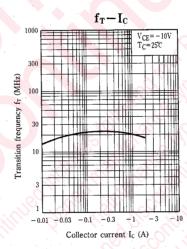
Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CES}	$V_{CE} = -60V, V_{BE} = 0$	10.		-200	μA
	I _{CEO}	$V_{CE} = -30V, I_B = 0$			-300	μA
Emitter cutoff current	I _{EBO}	$V_{EB} = -6V, I_C = 0$			-1	mA
Collector-emitter voltage	V_{CEO}	$I_{\rm C} = -30 \rm mA$, $I_{\rm C} = 0$	-60			V
DC current gain	h _{FE1}	$V_{CE} = -4V, I_{C} = -0.1A$	35			
	h _{FE2}	$V_{CE} = -4V$, $I_C = -1A$	100		280	
Base-emitter voltage	V_{BE}	$V_{CE} = -4V, I_{C} = -1A$		5	-1.2	V
Collector-emitter saturation voltage	V _{CE (sat)}	$I_C = -2A, I_B = -0.2A$			-2.0	. V
Transition frequency	f_{T}	$V_{CE} = -10V$, $I_C = 0.5A$, $f = 10MHz$		25		MHz
Turn-on time	t _{on}	T 14 T 074 T 074		0.5		μs
Storage time	t _{stg}	$I_C = -1A$, $I_{B1} = -0.1A$, $I_{B2} = 0.1A$ $V_{CC} = -50V$		1.2		μs
Collector current fall time	tf	- VCC - 30V	. 1	0.3	7.0	μs

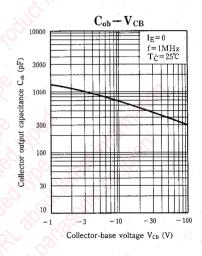


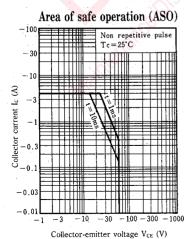












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